



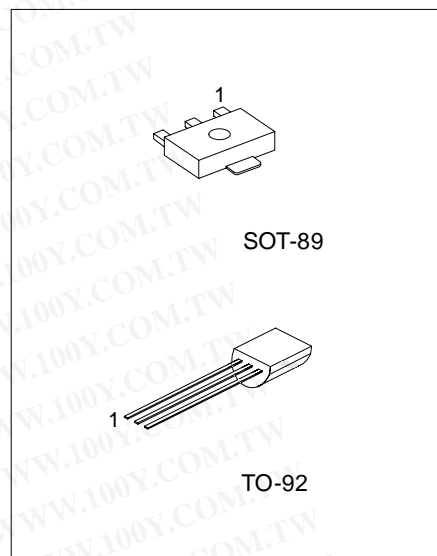
2N5401

PNP SILICON TRANSISTOR

HIGH VOLTAGE SWITCHING TRANSISTOR

FEATURES

- * Collector-emitter voltage:
 $V_{CE0} = -150V$
- * High current gain



*Pb-free plating product number:2N5401L

ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
2N5401-x-AB3-R	2N5401L-x-AB3-R	SOT-89	B	C	E	Tape Reel
2N5401-x-T92-B	2N5401L-x-T92-B	TO-92	E	B	C	Tape Box
2N5401-x-T92-K	2N5401L-x-T92-K	TO-92	E	B	C	Bulk

<p>2N5401L-x-AB3-R</p>	<ul style="list-style-type: none"> (1)Packing Type (2)Package Type (3)Rank (4)Lead Plating 	<ul style="list-style-type: none"> (1) B: Tape Box, K: Bulk, R: Tape Reel (2) AB3: SOT-89, T92: TO-92 (3) x: refer to Classification of h_{FE} (4) L: Lead Free Plating Blank: Pb/Sn
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勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

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■ ABSOLUTE MAXIMUM RATING (Ta=25°C , unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	-160	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-600	mA
Collector Dissipation	TO-92	625	mW
	SOT-89	500	mW
Junction Temperature	T _J	+150	
Storage Temperature	T _{STG}	-55 ~ +150	

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C = -100μA, I _E = 0	-160			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = -1mA, I _B = 0	-150			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = -10μA, I _C = 0	-6			V
Collector Cut-off Current	I _{CBO}	V _{CB} = -120V, I _E = 0			-50	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = -3V, I _C = 0			-50	nA
DC Current Gain(Note)	h _{FE1}	V _{CE} = -5V, I _C = -1mA	80			
	h _{FE2}	V _{CE} = -5V, I _C = -10mA	80		400	
	h _{FE3}	V _{CE} = -5V, I _C = -50mA	80			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C = -10mA, I _B = -1mA I _C = -50mA, I _B = -5mA			-0.2 -0.5	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C = -10mA, I _B = -1mA I _C = -50mA, I _B = -5mA			-1 -1	V
Current Gain Bandwidth Product	f _T	V _{CE} = -10V, I _C = -10mA f = 100MHz	100		400	MHz
Output Capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz			6.0	pF
Noise Figure	NF	I _C = -0.25mA, V _{CE} = -5V R _S = 1kΩ, f = 10Hz ~ 15.7kHz			8	dB

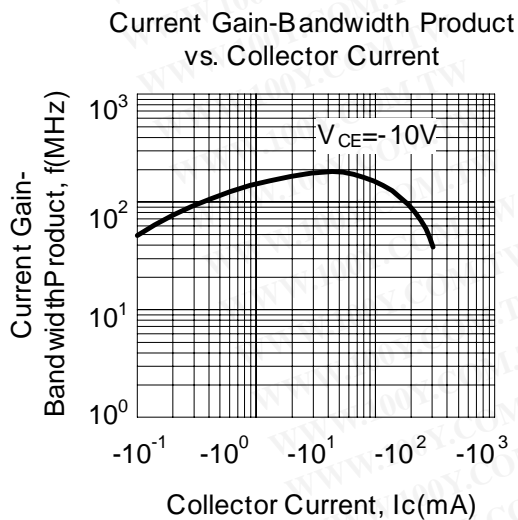
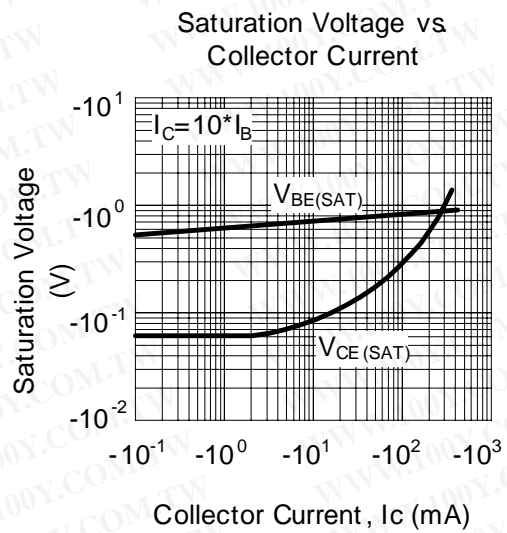
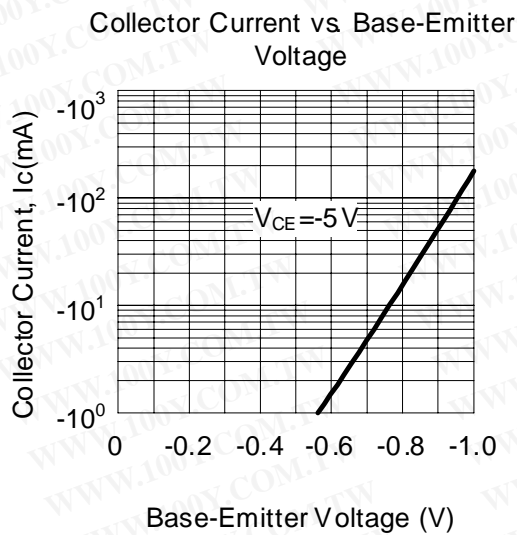
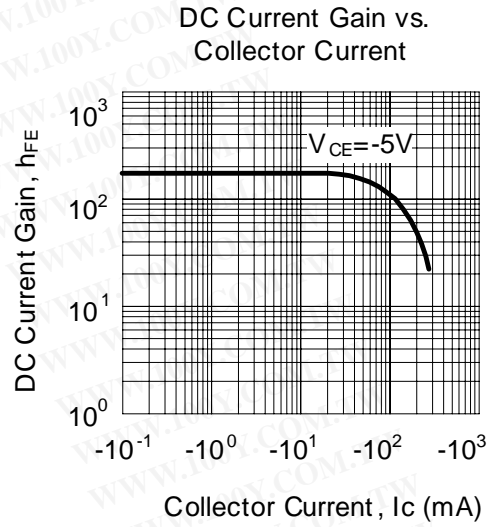
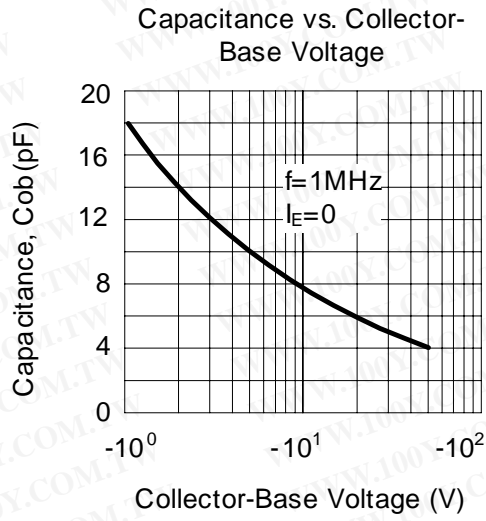
Note: Pulse test: PW<300μs, Duty Cycle<2%

■ CLASSIFICATION OF h_{FE}

RANK	A	B	C
RANGE	80-170	150-240	200-400

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TYPICAL CHARACTERISTICS



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